# **Excellent Integrated System Limited**

Stocking Distributor

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TT Electronics/Optek Technology OP804SL

For any questions, you can email us directly: sales@integrated-circuit.com

**Electronics** 

"WSL"

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# **NPN Phototransistor**

# OP800SL Series, OP800WSL Series OP830SL Series, OP830WSL Series

#### Features:

- TO-18 hermetically sealed package
- Mechanically and spectrally matched to OP130 and OP230 LEDs
- TX and TXV process available (see Hi-Rel section)
- · Choice of narrow or wide receiving angle
- Variety of sensitivity ranges
- Enhanced temperature range



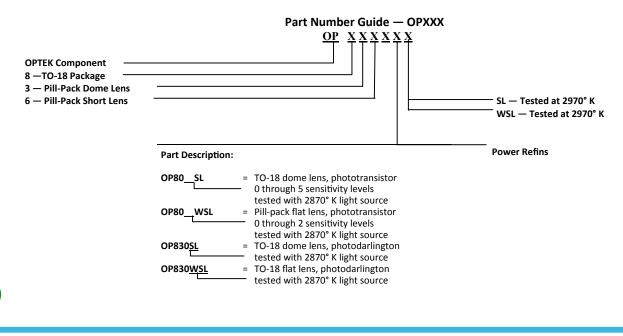
Each device in this series consists of a NPN silicon phototransistor mounted in a hermetically sealed TO-18 package that offers high power dissipation and superior hostile environment operation. The **OP800SL** and **OP830SL** devices have a narrow receiving angle that provides excellent on-axis coupling and a bonded base lead that enables conventional transistor biasing. The **OP800WSL**, **OP801WSL**, **OP802WSL** and **OP830WSL** all have a wide receiving angle that provides relatively even reception over a large area.

Devices are 100% production tested using an infrared light source for close correlation with OPTEK's GaAs and GaAlAs emitters. The OP800SL and devices are mechanically and spectrally matched to OP130 and OP230 series LEDs. The OP800WSL devices are mechanically and spectrally matched to OP130W and OP230W series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

### Applications:

- Space-limited applications
- Hostile environment applications
- · Applications requiring high power dissipation





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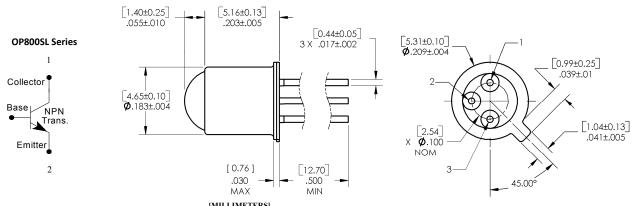
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## **NPN Phototransistor**

OP800SL Series. OP800WSL Series OP830SL Series, OP830WSL Series

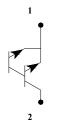


#### OP800SL, OP830SL



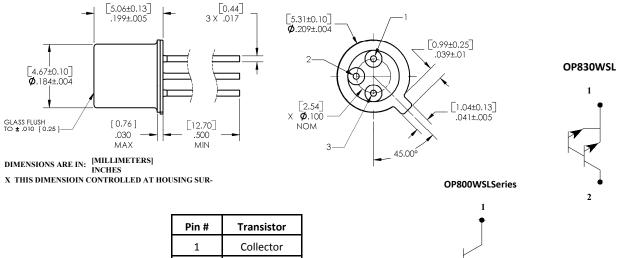
OP830SL

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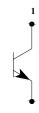


Pin#	Transistor		
1	Collector		
2	Base		
3	Emitter		

### OP800WSL, OP830WSL



2 Base
3 Emitte



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## **NPN Phototransistor**

OP800SL Series, OP800WSL Series OP830SL Series, OP830WSL Series



## **Electrical Specifications**

Absolute Maximum Ratings (T <sub>A</sub> = 25° C unless otherwise noted)	
Storage Temperature Range	-65° C to +150° C
Operating Temperature Range	-65° C to +125° C
Collector-Base Voltage (applies to OP800SL only - does not apply to OP800WSL)	30 V
Collector-Emitter Voltage OP800 (SL, WSL) OP830 (SL, WSL)	30 V 15 V
Emitter-Base Voltage (applies to OP800 (SL, WSL) only)	5 V
Emitter-Collector Voltage (applies to all OP800 and OP830 devices)	5 V
Continuous Collector Current	50 mA
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(1)</sup>
Power Dissipation	250 mW <sup>(2)</sup>

#### Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly 2.5 mW/° C above 25° C.
- 3. Junction temperature maintained at 25° C.



Datasheet of OP804SL - PHOTOTRANSISTOR NPN 890NM TO-18

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## **NPN Phototransistor**

OP800SL Series, OP800WSL Series OP830SL Series, OP830WSL Series



## **Electrical Specifications**

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
I <sub>C(ON)</sub> <sup>(3)</sup>	On-State Collector Current OP800SL	0.5 0.5	-	- 3			
	OP801SL OP802SL OP803SL OP804SL OP805SL OP800WSL	2.0	_	5	ν <sub>CE</sub> = 5 V, E <sub>E</sub> = 5	V <sub>CE</sub> = 5 V, E <sub>E</sub> = 5 mW/cm <sup>2(4)(5)</sup>	
		4.0	-	8			
		7.0	-	22			
		15	-	-			
C(OIV)		0.3	-	3			
	OP801WSL	0.5	-	2			
	OP802WSL	2.5	-	3			
	OP830SL	15	-	-		V <sub>CE</sub> = 5 V, E <sub>E</sub> = 0.5 mW/cm <sup>2(5)</sup>	
	OP830WSL	4	-	-			
I <sub>CEO</sub>	Collector Dark Current				nA V <sub>CE</sub> = 1		
	OP800 (SL, WSL)	-	-	100		$V_{CE} = 10 \text{ V}, E_{E} = 0$	
	OP830 (SL, WSL)	-	-	1			
	Collector-Emitter Breakdown Voltage						
V <sub>(BR)CEO</sub>	OP800 (SL, WSL)	30	-	-	V	I <sub>C</sub> = 100 μA	
	OP830 (SL, WSL)	15	-	-			
V <sub>(BR)CBO</sub>	Collector- <b>Base</b> Breakdown Voltage	30	_	_	V	Ι <sub>c</sub> = 100 μΑ	
	[applies to OP800SL only]				-	7 200 p	
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0	-	-	V	Ι <sub>Ε</sub> = 100 μΑ	
V <sub>(BR)EBO</sub>	Emitter- <b>Base</b> Breakdown Voltage	5.0	_		V	I <sub>F</sub> = 100 μA	
	[applies to OP800SL only]	3.0	_		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	η - 100 μΑ	
V <sub>CE(SAT)</sub> <sup>(3)</sup>	Collector-Emitter Saturation Voltage					2(4)	
	OP800WSL	-	-	0.4	,,	$I_C = 0.15 \text{ mA}, E_E = 0.5 \text{ mW/cm}^{2(4)}$	
	OP800SL	-	-	0.4 1.2	V	$I_C = 0.4 \text{ mA}, E_E = 5 \text{ mW/cm}^{2(5)}$	
	OP830SL	_	_	1.2		$I_C = 0.15 \text{ mA}, E_E = 0.5 \text{ mW/cm}^{2(5)}$	
	OP830WSL					$I_C = 1.0 \text{ mA}, E_E = 0.5 \text{ mW/cm}^{2(5)}$	
t <sub>r</sub>	Rise Time	-	7	-	μs	$V_{CC} = 5 \text{ V, } I_C = 0.80 \text{ mA,}$ $R_L = 100 \Omega \text{ (See Test Circuit)}$	
$t_f$	Fall Time	-	7	-	μs		

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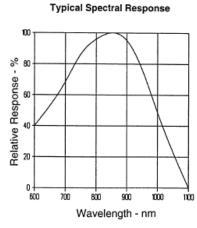
## **NPN Phototransistor**

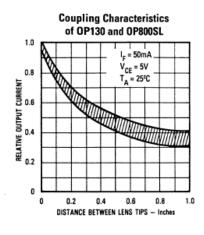
OP800SL Series, OP800WSL Series OP830SL Series, OP830WSL Series

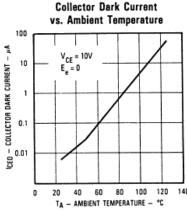


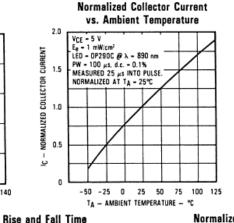
### Performance

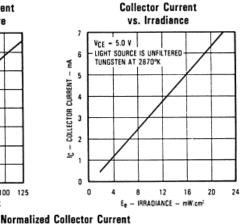
#### **OP800SL Series**

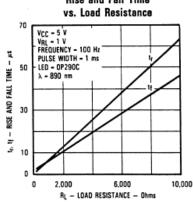


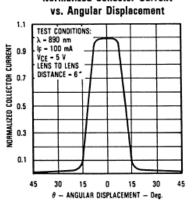












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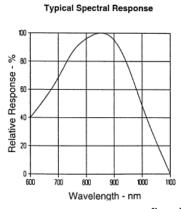
## **NPN Phototransistor**

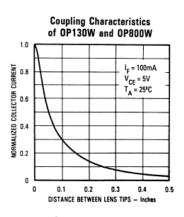
OP800SL Series, OP800WSL Series OP830SL Series, OP830WSL Series



### Performance

#### **OP800WSL Series**





Collector Dark Current vs. Ambient Temperature

100

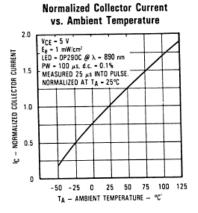
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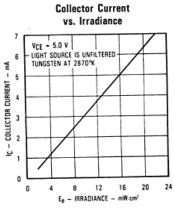
Ee= 0

100

20 40 60 80 100 120 140

TA - AMBIENT TEMPERATURE - °C

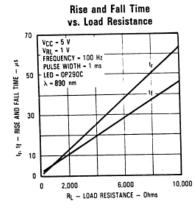


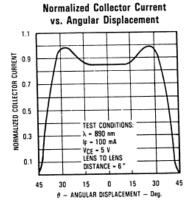


Rise and Fall Time vs. Load Resistance

Normalized Collector Current vs. Angular Displacement

Switching Time Test Circuit





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## **NPN Phototransistor**

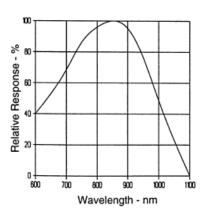
OP800SL Series. OP800WSL Series OP830SL Series, OP830WSL Series

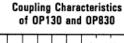


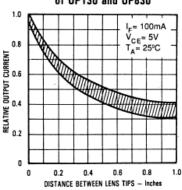
### Performance

#### **OP830SL Series**

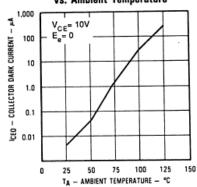




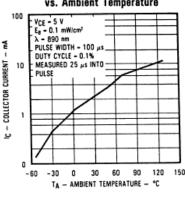




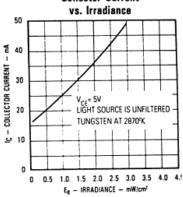
#### Collector Dark Current vs. Ambient Temperature



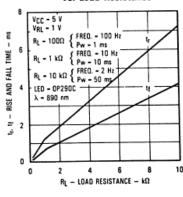
### **Collector Current** vs. Ambient Temperature



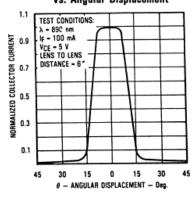
**Collector Current** 



#### Rise and Fall Time vs. Load Resistance



#### **Normalized Collector Current** vs. Angular Displacement



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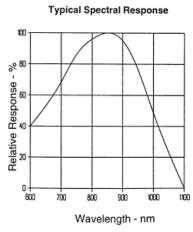
## **NPN Phototransistor**

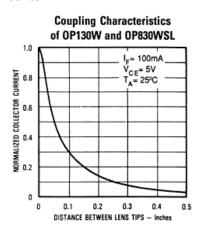
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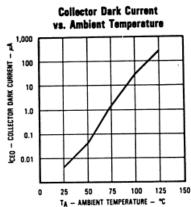


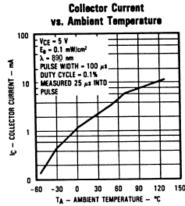
### Performance

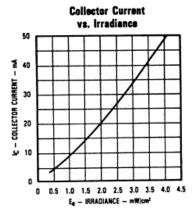
#### **OP830WSL Series**

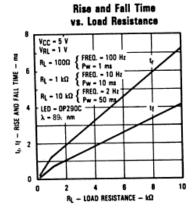


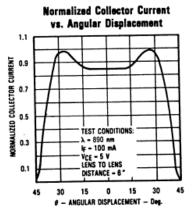












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